

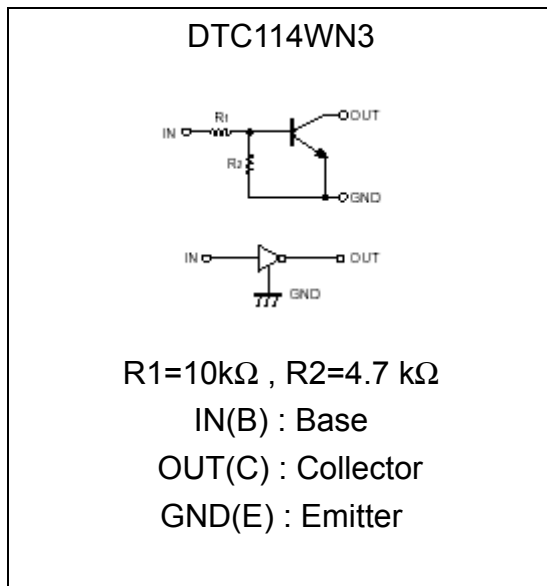
**NPN Digital Transistors (Built-in Resistors)**

# DTC114WN3

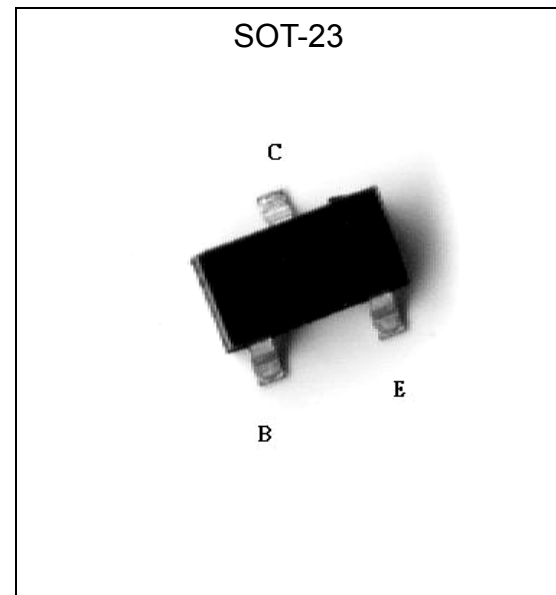
**Features**

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, making device design easy.
- Complements the DTA114WN3
- Pb-free lead plating and halogen-free package.

**Equivalent Circuit**

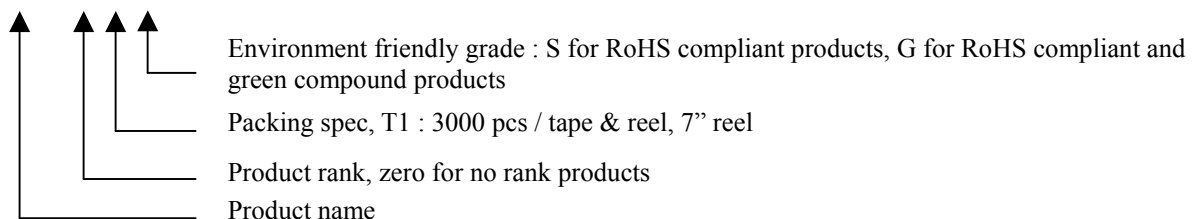


**Outline**



**Ordering Information**

| Device           | Package   | Shipping               |
|------------------|---|------------------------|
| DTC114WN3-0-T1-G | SOT-23<br>(Pb-free lead plating and halogen-free package) | 3000 pcs / tape & reel |





**Absolute Maximum Ratings (Ta=25°C)**

| Parameter                               | Symbol               | Limits   | Unit |
|---|----------------------|----------|------|
| Supply Voltage                          | V <sub>CC</sub>      | 50       | V    |
| Input Voltage                           | V <sub>I</sub>       | -10~+30  | V    |
| Output Current                          | I <sub>O</sub>       | 100      | mA   |
|   | I <sub>O(max.)</sub> | 100      | mA   |
| Power Dissipation                       | P <sub>D</sub>       | 200      | mW   |
| Thermal Resistance, Junction to Ambient | R <sub>θJA</sub>     | 625      | °C/W |
| Operating Junction Temperature Range    | T <sub>j</sub>       | -55~+150 | °C   |
| Storage Temperature Range               | T <sub>stg</sub>     | -55~+150 | °C   |

**Electrical Characteristics (Ta=25°C)**

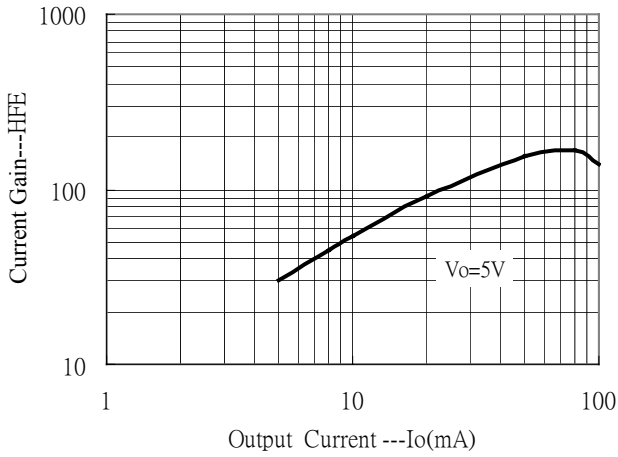
| Parameter            | Symbol                         | Min. | Typ. | Max. | Unit | Test Conditions                                       |
|----------------------|--------------------------------|------|------|------|------|---|
| Input Voltage        | V <sub>I(off)</sub>            | -    | -    | 0.8  | V    | V <sub>CC</sub> =5V, I <sub>O</sub> =100μA            |
|                      | V <sub>I(on)</sub>             | 3    | -    | -    | V    | V <sub>O</sub> =0.3V, I <sub>O</sub> =2mA             |
| Output Voltage       | V <sub>O(on)</sub>             | -    | -    | 0.3  | V    | I <sub>O</sub> /I <sub>I</sub> =10mA/0.5mA            |
| Input Current        | I <sub>I</sub>                 | -    | -    | 0.88 | mA   | V <sub>I</sub> =5V                                    |
| Output Current       | I <sub>O(off)</sub>            | -    | -    | 0.5  | μA   | V <sub>CC</sub> =50V, V <sub>I</sub> =0V              |
| DC Current Gain      | G <sub>I</sub>                 | 24   | -    | -    | -    | V <sub>O</sub> =5V, I <sub>O</sub> =10mA              |
| Input Resistance     | R <sub>I</sub>                 | 7    | 10   | 13   | kΩ   | -   |
| Resistance Ratio     | R <sub>2</sub> /R <sub>1</sub> | 0.37 | 0.47 | 0.57 | -    | -   |
| Transition Frequency | f <sub>T</sub>                 | -    | 250  | -    | MHz  | V <sub>CE</sub> =10V, I <sub>C</sub> =5mA, f=100MHz * |

\* Transition frequency of the device

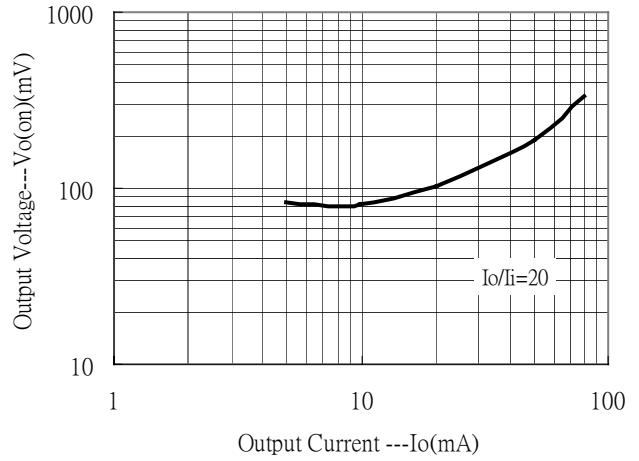


### Typical Characteristics

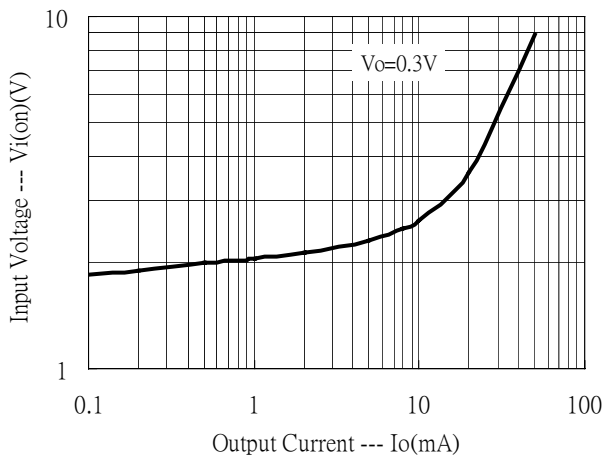
DC Current Gain vs Output Current



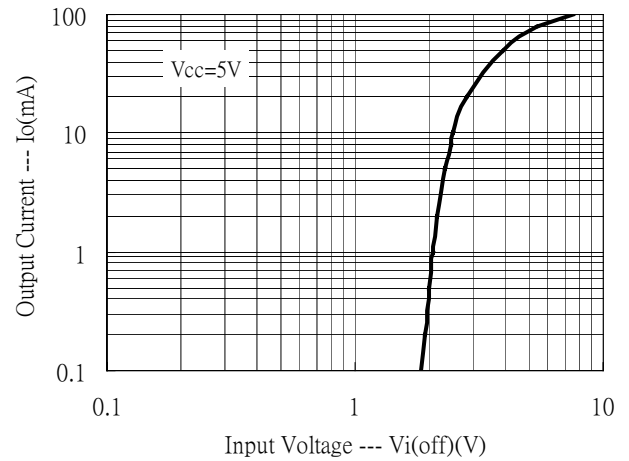
Output Voltage vs Output Current



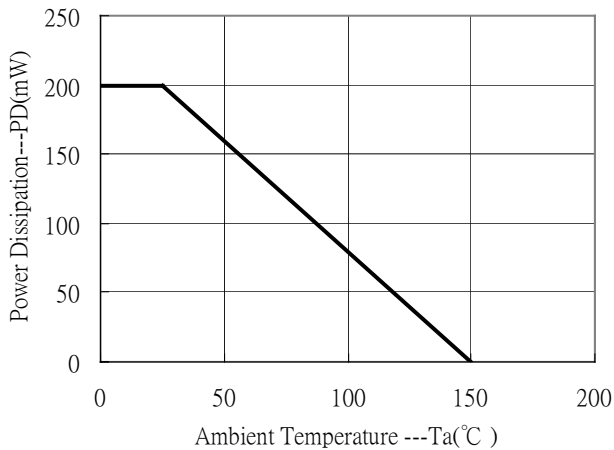
Input Voltage vs Output Current (ON Characteristics)



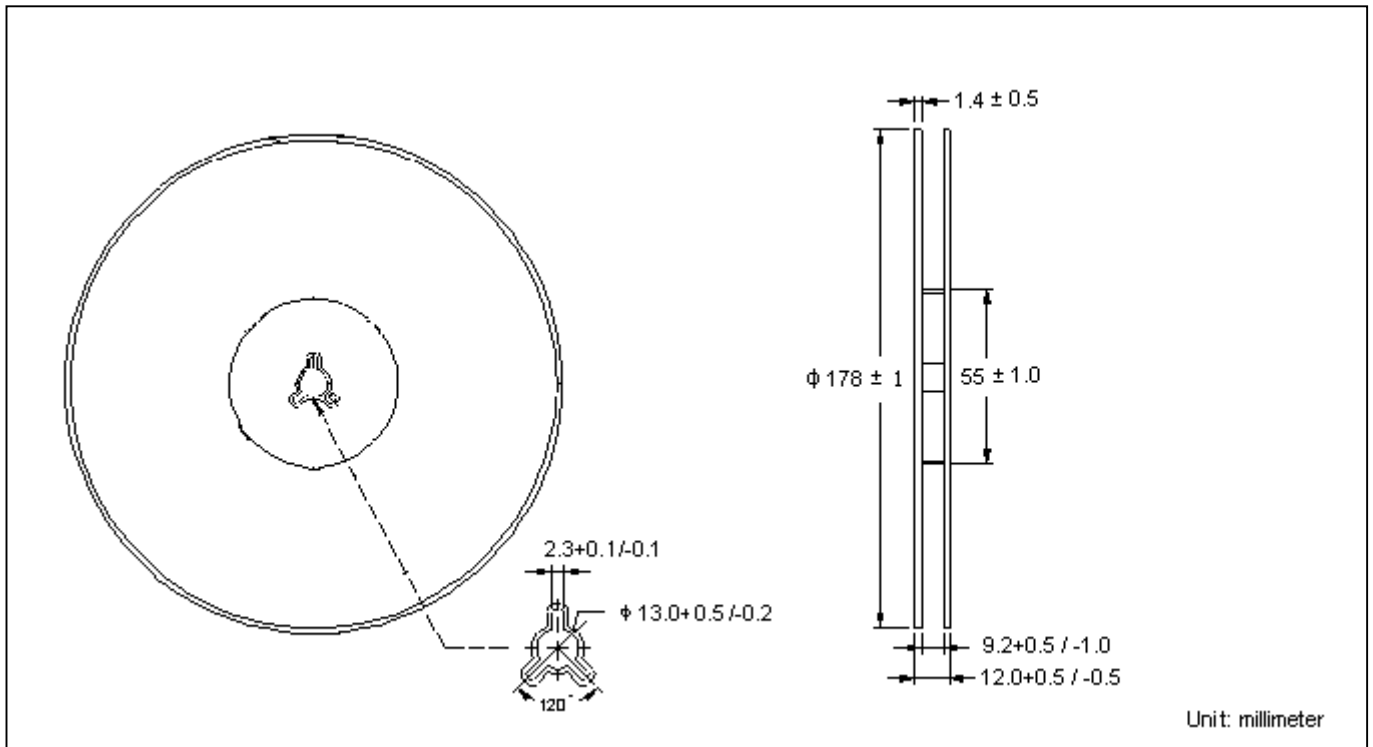
Output Current vs Input Voltage (OFF Characteristics)



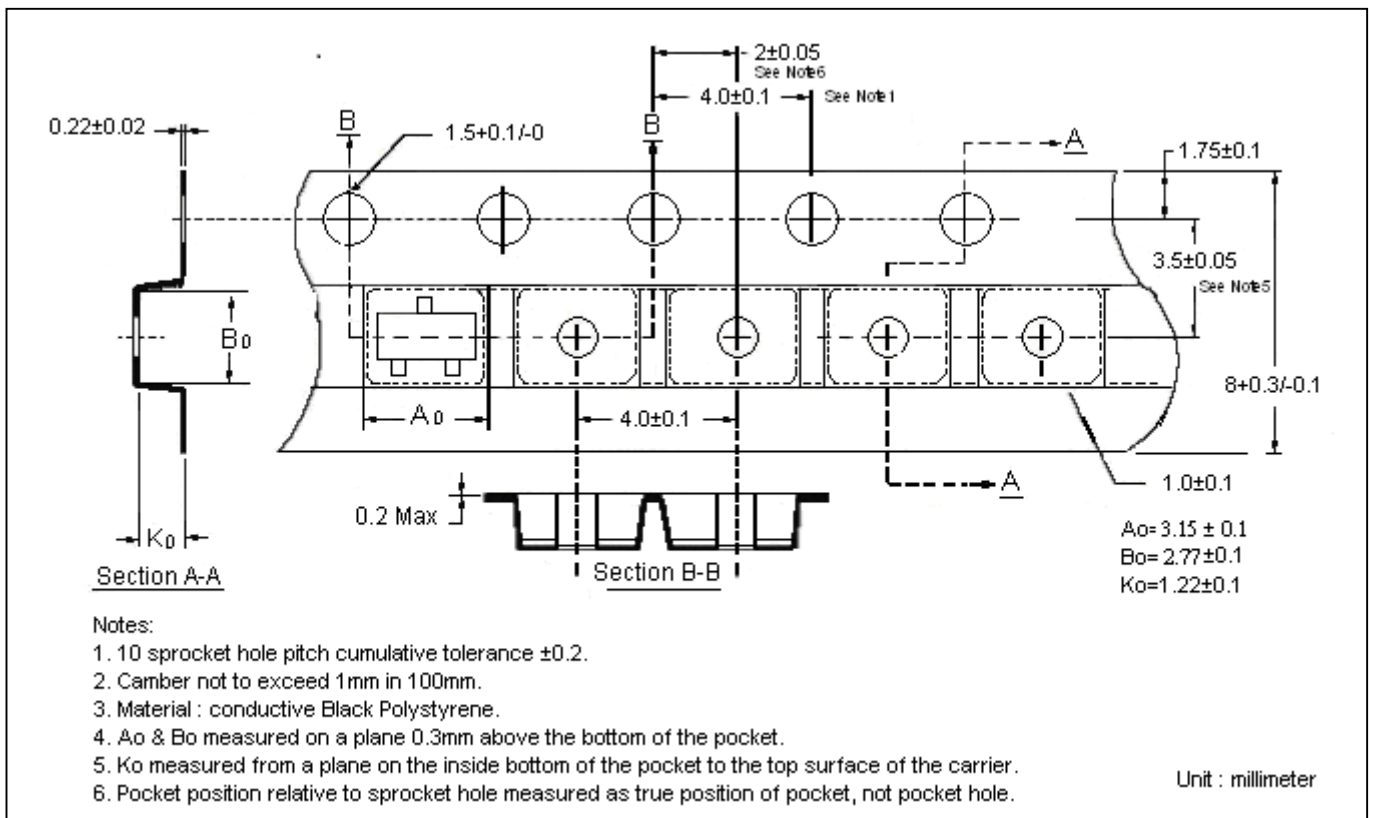
Power Derating Curve



**Reel Dimension**



**Carrier Tape Dimension**

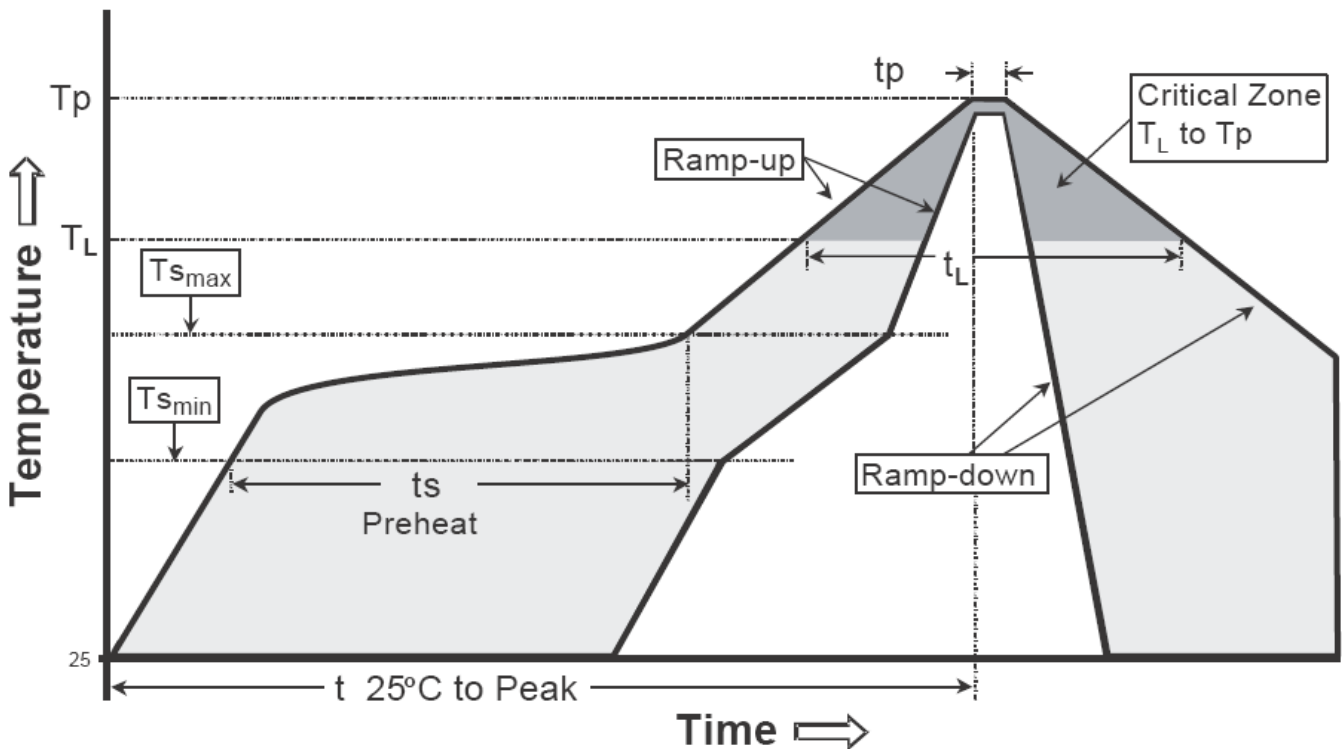


**Notes:**

1. 10 sprocket hole pitch cumulative tolerance  $\pm 0.2$ .
2. Camber not to exceed 1mm in 100mm.
3. Material : conductive Black Polystyrene.
4. Ao & Bo measured on a plane 0.3mm above the bottom of the pocket.
5. Ko measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

**Recommended wave soldering condition**

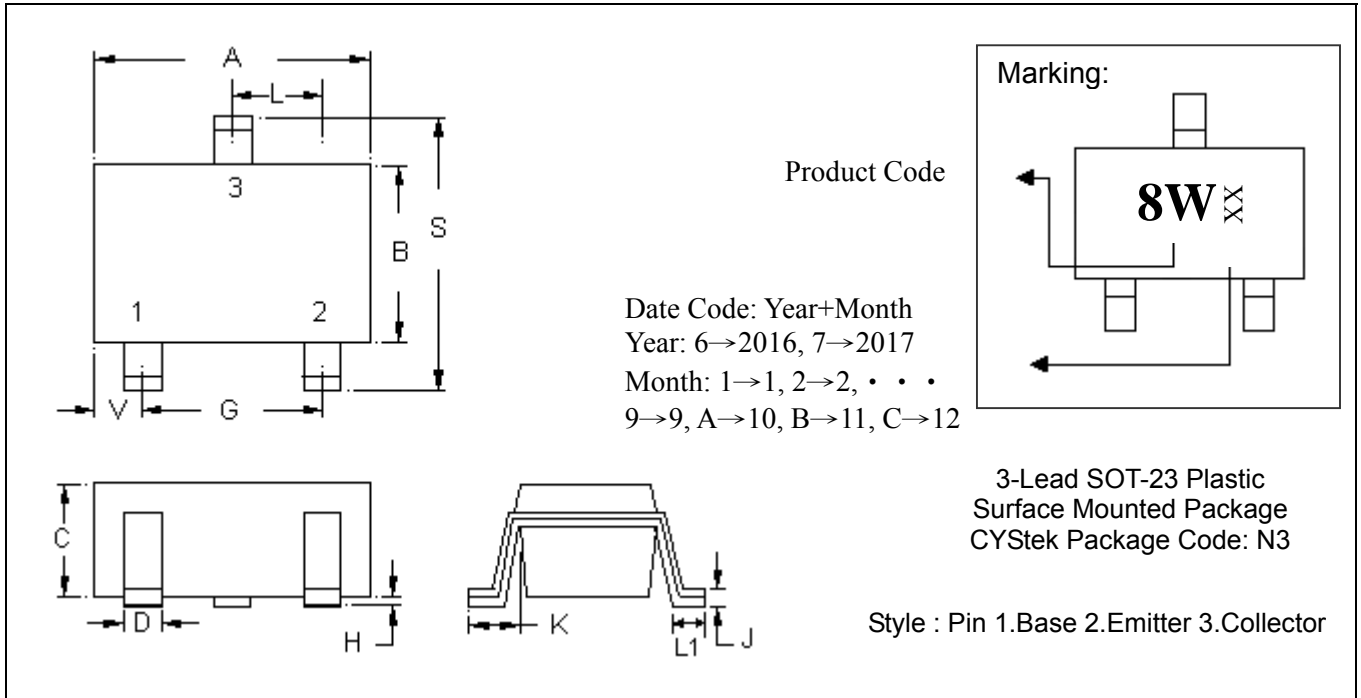
|                 |                  |                 |
|-----------------|------------------|-----------------|
| Product         | Peak Temperature | Soldering Time  |
| Pb-free devices | 260 +0/-5 °C     | 5 +1/-1 seconds |

**Recommended temperature profile for IR reflow**


| Profile feature   | Sn-Pb eutectic Assembly | Pb-free Assembly |
|---|-------------------------|------------------|
| Average ramp-up rate (T <sub>smax</sub> to T <sub>p</sub> ) | 3°C/second max.         | 3°C/second max.  |
| Preheat   |                         |                  |
| -Temperature Min(T <sub>s min</sub> )                       | 100°C                   | 150°C            |
| -Temperature Max(T <sub>s max</sub> )                       | 150°C                   | 200°C            |
| -Time(t <sub>s min</sub> to t <sub>s max</sub> )            | 60-120 seconds          | 60-180 seconds   |
| Time maintained above:                                      |                         |                  |
| -Temperature (T <sub>L</sub> )                              | 183°C                   | 217°C            |
| - Time (t <sub>L</sub> )                                    | 60-150 seconds          | 60-150 seconds   |
| Peak Temperature(T <sub>p</sub> )                           | 240 +0/-5 °C            | 260 +0/-5 °C     |
| Time within 5°C of actual peak temperature(tp)              | 10-30 seconds           | 20-40 seconds    |
| Ramp down rate  | 6°C/second max.         | 6°C/second max.  |
| Time 25 °C to peak temperature                              | 6 minutes max.          | 8 minutes max.   |

Note : All temperatures refer to topside of the package, measured on the package body surface.

**SOT-23 Dimension**



\*:Typical

| DIM | Inches |        | Millimeters |      | DIM | Inches |        | Millimeters |      |
|-----|--------|--------|-------------|------|-----|--------|--------|-------------|------|
|     | Min.   | Max.   | Min.        | Max. |     | Min.   | Max.   | Min.        | Max. |
| A   | 0.1102 | 0.1204 | 2.80        | 3.04 | J   | 0.0032 | 0.0079 | 0.08        | 0.20 |
| B   | 0.0472 | 0.0551 | 1.20        | 1.40 | K   | 0.0118 | 0.0266 | 0.30        | 0.67 |
| C   | 0.0335 | 0.0512 | 0.89        | 1.30 | L   | 0.0335 | 0.0453 | 0.85        | 1.15 |
| D   | 0.0118 | 0.0197 | 0.30        | 0.50 | S   | 0.0830 | 0.1004 | 2.10        | 2.55 |
| G   | 0.0669 | 0.0910 | 1.70        | 2.30 | V   | 0.0098 | 0.0256 | 0.25        | 0.65 |
| H   | 0.0000 | 0.0040 | 0.00        | 0.10 | L1  | 0.0118 | 0.0197 | 0.30        | 0.50 |

Notes : 1.Controlling dimension : millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material :**

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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